## isc N-Channel MOSFET Transistor

### **IRFZ44N**

#### **FEATURES**

- Drain Current –I<sub>D</sub>=49A@ T<sub>C</sub>=25℃
- · Drain Source Voltage-
  - : V<sub>DSS</sub>= 55V(Min)
- Static Drain-Source On-Resistance
  - :  $R_{DS(on)} = 0.032 \Omega (Max)$
- · Fast Switching

#### **DESCRIPTION**

 Designed for low voltage, high speed switching applications in power supplies, converters and power motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional safety margin against unexpected voltage transients.

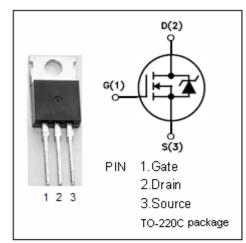
#### ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}$ C)

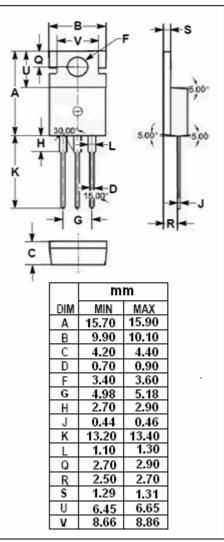
SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	55	V
V <sub>GS</sub>	Gate-Source Voltage-Continuous	±20	V
I <sub>D</sub>	Drain Current-Continuous 49		Α
I <sub>DM</sub>	Drain Current-Single Pluse (t <sub>p</sub> ≤10 μ s)		Α
P <sub>D</sub>	Total Dissipation @T <sub>C</sub> =25℃	94	W
TJ	Max. Operating Junction Temperature	ture 175	
T <sub>stg</sub>	Storage Temperature -55~175		$^{\circ}$ C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.5	°C/W
R <sub>th j-a</sub>	R <sub>th j-a</sub> Thermal Resistance, Junction to Ambient		°C/W

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#### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA	55		V
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS}$ = $V_{GS}$ ; $I_D$ = 0.25mA	2	4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 25A		0.032	Ω
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0		±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 55V; V <sub>GS</sub> = 0 V <sub>DS</sub> = 55V; V <sub>GS</sub> = 0; T <sub>j</sub> = 150 °C		25 250	μА
$V_{SD}$	Forward On-Voltage	I <sub>S</sub> = 25A; V <sub>GS</sub> = 0		1.3	V

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